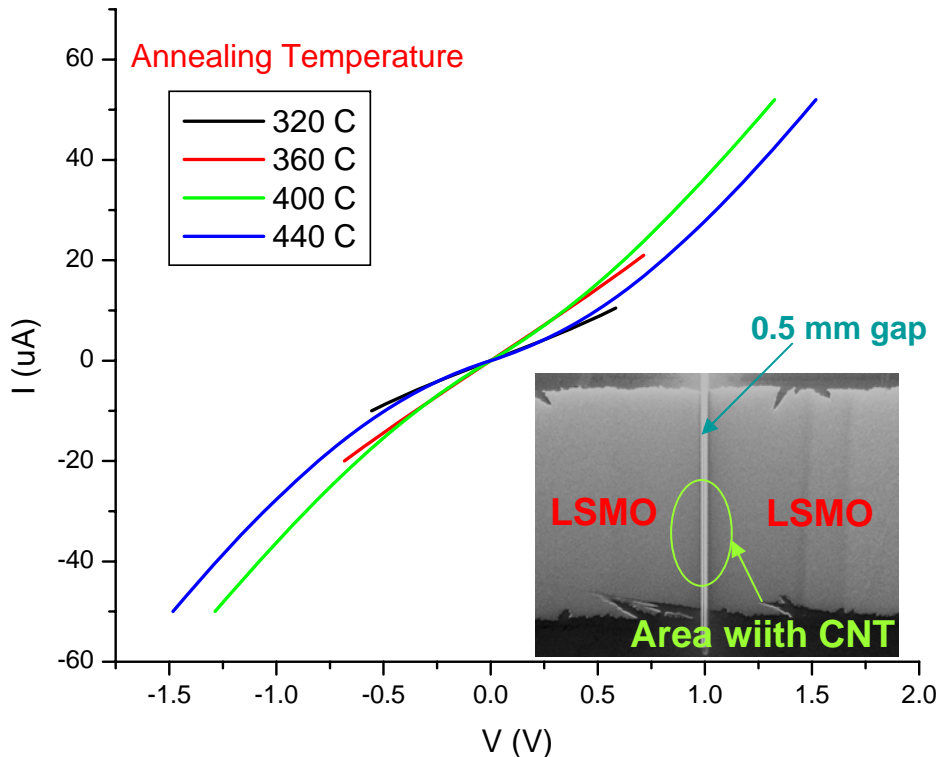


Effect of annealing on room temperature I-V of LSMO/CNT/LSMO lateral devices



Current increases upon low temperature annealing, but it starts to decrease for $T > 400$ C, indicating that 400C vacuum anneal is the optimal condition for LSMO/CNT interfaces.